

Serial No. 09/856,212

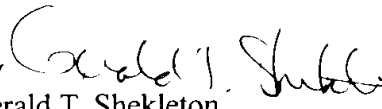
list each and every feature disclosed by each document. The Examiner is requested to review the document(s) and determine the extent of the materiality of the document disclosures with respect to the present invention.

The discussion of any art and the citation of any document(s) herein is not to be construed as an admission that the art or document disclosure is necessarily within the invention field of endeavor, that the art or document disclosure is necessarily prior in time to a particular date which may be relevant to the instant patent application, and/or that the art or document disclosure is otherwise necessarily prior art as defined by the patent law with respect to the instant invention and application.

Also, there is reserved the right to later set forth how the instant invention is distinguished over the disclosure of any document or other art, including the disclosures of the art and document(s) recited herein, that may be cited by the Examiner in rejecting a claim in the instant patent application. The recitation herein of the art and document(s) is not to be construed as an assertion that more pertinent art could not possibly be in existence.

Respectfully submitted,

WELSH & KATZ, LTD.

By 
Gerald T. Shekleton
Registration No. 27,466

Dated: June 23, 2003

Welsh & Katz, Ltd.

120 South Riverside Plaza, 22nd Floor
Chicago, Illinois 60606
Telephone: 312/655-1500



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Sheet 1 of 1

(Rev. 5/92) Comparable to Form PTO-1449 INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 82821	Serial No. 09/856,212
	Applicant NAKAMURA et al.		
	Filing Date May 18, 2001	Group 1765	

U.S. PATENT DOCUMENTS

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	4,437,922	03/20/1984	Bischoff et al.			
	4,944,834	07/31/1990	Tada et al.			
	6,036,776	03/14/2000	Kotooka et al.			

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Name of Patentee	Class	Subclass	Translation	
						Yes	No
	EP 0823497	02/11/1998	MEMC Electronic Materials, Inc.				
	EP 0866150	09/23/1998	Wacker Siltronic Gesellschaft fur				
	EP 0785298	06/26/2002	MEMC Electronic Materials, Inc.				
	JP 03-279290	12/10/1991	Osaka Titanium Co., Ltd.				
	JP 05-194076	08/03/1993	Komatsu Denshi Kinzoku KK				
	JP 07-133187	05/23/1995	Komatsu Electron Metals Co., Ltd.				
	WO 98/45507	10/15/1998	MEMC Electronic Materials, Inc.				
	WO 98/45508	10/15/1998	MEMC Electronic Materials, Inc.				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	NAKAMURA, KOZO et al.: "Formation process of grown-in defects in Czochralski grown silicon crystals" JOURNAL OF CRYSTAL GROWTH 180 (1997) 61-72
	AMMON, WILFRIED VON et al.: "The dependence of bulk defects on the axial temperature gradient of silicon crystals during Czochralski growth" 2300 JOURNAL OF CRYSTAL GROWTH 151 (1995) June 1, Nos. 3/4, Amsterdam, NL, Pages 273-277

Examiner	Date Considered
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*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.